

U.S. Patent Application Serial No. 09/456,531
Response dated September 2, 2003
Reply to OA of June 3, 2003

IN THE CLAIMS:

Please cancel claim 13 without prejudice or disclaimer.

Please amend claim 3 as follows:

1. (Previously Presented): An electrode structure including a bonding pad formed on an insulation film without penetrating the insulation film, the insulation film being formed above a base substrate,

the insulation film comprising a plurality of poles of polyimide, a first film formed on each side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on the side surfaces thereof.

2. (Canceled).

3. (Currently Amended): A semiconductor light-emitting device having a waveguide including an active layer or a light absorption layer, a lower electrode formed below the waveguide, and an upper electrode formed above the waveguide,

the upper electrode having an electrode structure,

an the electrode structure including a bonding pad formed on an insulation film without penetrating the insulation film, the insulation film being formed above a base substrate,


the insulation film comprising a plurality of poles of polyimide, a first film formed on each side surfaces of the poles and formed of an insulation material having a higher hardness than

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polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on side surfaces thereof.

4. (Original): A semiconductor light-emitting device according to claim 3, wherein the first film is also formed on upper surfaces of the poles.

5. (Canceled).

 6. (Previously Presented): A semiconductor light-emitting device according to claim 3, wherein the first film is also formed on upper surfaces of the second film.

7. (Previously Presented): A semiconductor light-emitting device according to claim 3, wherein a third film of an insulation material is sandwiched between the insulation film and the bonding pad.

8 - 10. (Canceled).

11. (Previously Presented): A semiconductor light-emitting device according to claim 3, wherein

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the insulation film is formed on a layer formed on the base substrate, the layer being formed of a material having a higher hardness than the polyamide.

12-14. (Canceled).

15. (Previously Presented): A semiconductor light-emitting device according to claim 13, further comprising

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a high resistance layer formed on a side of the waveguide; and
said electrode structure formed on the high resistance layer.

16-18. (Canceled).

19. (Previously Presented): An electrode structure according to claim 1, wherein the first film is also formed on upper surfaces of the poles.

20. (Previously Presented): An electrode structure according to claim 1, wherein the first film is also formed on upper surfaces of the second film.

21. (Previously Presented): A semiconductor light-emitting device according to claim 13, wherein

the first film is also formed on upper surfaces of the poles.

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22. (Previously Presented): A semiconductor light-emitting device according to claim 13,
wherein

the first film is also formed on upper surfaces of the second film.
